Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13260	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/e21.179) or (257/e21.422) or (257/e21.68) or (365/185.12) or (365/185.13) or (365/185.17) or (365/185.18) or (365/185.19) or (365/185.28)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:42
L2	0	1 and memory and (select access) near2 (transistor MOS MOSFET) and floating adj gate and "well" and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:45
L3	119	1 and memory and (select access) near2 (transistor MOS MOSFET) and floating adj gate and "well" and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation) implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:49
L4	1	((liu near2 i-sheng).in. (chang near2 shang-de).in. programmable adj microelectronics.as. chingis.as.) and memory.clm. and (select access) near2 (transistor MOS MOSFET).clm. and floating adj gate.clm. and "well".clm. and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation) implant).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:51
S1	5	"753673".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 23:05
S2	2	("5761121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:16
S3	2	EP-776049$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:19

EAST Search History (13 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13260	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/e21.179) or (257/e21.422) or (257/e21.68) or (365/185.12) or (365/185.13) or (365/185.17) or (365/185.18) or (365/185.19) or (365/185.28)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:42
L2	0	1 and memory and (select access) near2 (transistor MOS MOSFET) and floating adj gate and "well" and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:45
L3	119	1 and memory and (select access) near2 (transistor MOS MOSFET) and floating adj gate and "well" and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation) implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:49
L4	1	((liu near2 i-sheng).in. (chang near2 shang-de).in. programmable adj microelectronics.as. chingis.as.) and memory.clm. and (select access) near2 (transistor MOS MOSFET).clm. and floating adj gate.clm. and "well".clm. and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation) implant).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 20:02
L5	1	((liu near2 i-sheng).in. (chang near2 shang-de).in. programmable adj microelectronics.as. chingis.as.) and memory.clm. and (select access) near2 (transistor MOS MOSFET).clm. and floating adj gate.clm. and "well".clm. and (punch$1through punch adj through) and ("high substrate" near2 (doping implant implantation) implant).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/28 20:02
S1	5	"753673".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 23:05

EAST Search History

S2	2	("5761121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:16
S3	2	EP-776049$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:19
S4	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:23
S5	0	("two-transistornear3(PMOSPMOSFET)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:24
S6	2	two-transistor near3 (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:29
S7	574	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:30
S8	115	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET) and select adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:31
S9	115	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET) and select adj gate and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:54
S10	10	implant near6 common near2 (drain source "source/drain") and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:55
S11	10	(halo implant) near6 common near2 (drain source "source/drain") and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:55

EAST Search History

S12	2	(US-6207991-$ or US-5877051-$).did.	USPAT	OR	OFF	2005/02/22 08:04
S13	12	(US-20050030827-$ or US-20030034510-$).did. or (US-5761121-$ or US-5912842-$ or US-5943265-$ or US-5687118-$ or US-6207991-$ or US-5877051-$ or US-6146936-$).did. or (EP-776049-$ or WO-9919880-$).did. or (EP-776049-$).did.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 08:08
S14	215	two adj transistor near4 memory adj cell	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 08:08
S15	99	two adj transistor near4 memory adj cell and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2005/02/22 08:09
S16	99	two adj transistor near4 memory adj cell and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:13
S17	249	implant and (punch-through punch adj "through") and common adj (source drain "source/drain")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:15
S18	190	implant and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:15
S19	39	implant and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:22
S20	39	(halo implant) and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:24
S21	0	halo near6 punch-through and halo near6 common near2 (source-drain source/drain drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:25
S22	6	halo near6 (punchthrough punch adj through punch-through) and common near2 (source-drain source/drain drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:42

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S23	7	chang.in. and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:52
S24	2	S23 and polysilicon and (bit adj line bitline bit adj line) and floating adj gate and select adj gate and (tunneling tunnelling) near3 (Fowler Nordheim) and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:39
S25	1	S23 and polysilicon and (bit adj line bitline bit adj line) and control adj gate near6 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:52
S26	0	S23 and polysilicon and floating adj gate and control adj gate near6 (body adj bias back-gate back adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:53
S27	49	control adj gate near6 (body adj bias back-gate back adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:54
S28	26	control adj gate near6 (body adj bias back-gate back adj gate) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:55
S29	7	control adj gate near6 (body adj bias back-gate back adj gate) and floating adj gate and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:56
S30	12	(US-20050030827-$ or US-20030034510-$).did. or (US-5761121-$ or US-5912842-$ or US-5943265-$ or US-5687118-$ or US-6207991-$ or US-5877051-$ or US-6146936-$).did. or (EP-776049-$ or WO-9919880-$).did. or (EP-776049-$).did.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 10:27
S31	0	S30 and (thick thickness) near4 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:28
S32	1	S30 and (depth thick thickness) near4 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:30

S33	33	(depth thick thickness) near4 (drain source) and floating adj gate and halo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:50
S34	278	"100" near2 kev near10 phosphorus same implantation and (depth thickness thick)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:52
S35	12	"100" near2 kev near10 phosphorus near10 (depth thickness) same implantation and (depth thickness thick)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:09
S36	5789	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/e21. 179) or (257/e21.422) or (257/e21. 68)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:10
S37	15	S36 and (halo implant) and floating adj gate and punch adj through and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12
S38	1151	(365/185$2).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12
S39	5	S38 and (halo implant) and floating adj gate and punch adj through and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12
S40	718	halo adj implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:09
S41	48	halo adj implant and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:20
S42	310	(counter-doped halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:21

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S43	383	(counter adj dop$3 halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:21
S44	398	(counter adj dop$3 halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:47
S45	0	floating adj gate near20 (logic$2 address select) adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:47
S46	1149	floating adj gate near20 ((logic$2 address select) adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48
S47	0	floating adj gate near20 ((logic$2 address select) adj gate) and halo near4 "only"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48
S48	0	floating adj gate near20 ((logic$2 address select) adj gate) and halo near4 ("exclusively" "only")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48
S49	0	floating adj gate near20 ((logic$2 address select) adj gate) and halo near4 ("exclusively" "only" "one" adj side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:49
S50	27	floating adj gate near20 ((logic$2 address select) adj gate) and halo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:09
S51	184	floating adj gate near20 ((logic$2 address select) adj gate) and buried	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:40
S52	0	floating adj gate near20 ((logic$2 address select) adj gate) and counter adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:40

S53	203	floating adj gate near20 ((logic$2 address select) adj gate) and (counter adj dop$3 buried halo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:04
S54	7	punch adj "through" near6 (oxynitride ONO roxnox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:08
S55	2	("6180443").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:08
S56	2	S55 and implant$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:10
S57	304	floating near1 gate and (select logic$2 address) near1 gate and punch adj through	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:13
S58	1062	floating near1 gate and (control select logic$2 address) near1 gate and punch adj through	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14
S59	1802	floating near1 gate and (control select logic$2 address) near1 gate and (over adj erase punch adj through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14
S60	1802	floating near1 gate and (control select logic$2 address) near1 gate and ("over" adj erase punch adj through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14
S61	500	floating near1 gate and (control select logic$2 address) near1 gate and ("over" adj erase punch adj through) and (buried counter adj dop$3 halo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:17
S62	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 16:42

S63	9458	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/E21.179) or (257/E21.422) or (365/185.12) or (365/185.13) or (365/185.17) or (365/185.18) or (365/185.29)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 16:43
S64	29	S63 and floating and (halo counter adj dop$3 buried) near10 (punch adj "through")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 16:44
S65	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 23:07
S66	2	"20040070030".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 23:16
S67	10043	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/e21.179) or (257/e21.422) or (257/e21.68) or (365/185.12) or (365/185.13) or (365/185.17) or (365/185.18)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 19:42
S68	23	S67 and ("low" "lower" decrease decreasing improvement improve improving) near4 threshold and (implant buried) and common adj ("source/drain" "S/D" source-drain (source adj drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:25
S69	24	S67 and ("low" "lower" decrease decreasing improvement improve improving) near4 threshold and (implant buried halo) and common adj ("source/drain" "S/D" source-drain (source adj drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:27
S70	27	S67 and ("low" "lower" decrease decreasing improvement improve improving) near4 threshold and (implant buried halo) and common adj ("source/drain" "S/D" source-drain (source near2 drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:28

S71	63	S67 and ("low" "lower" decrease decreasing improvement improve improving) near4 threshold and common adj ("source/drain" "S/D" source-drain (source near2 drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:31
S72	342	("low" "lower" decrease decreasing improvement improve improving) near4 threshold and common adj ("source/drain" "S/D" source-drain (source near2 drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:32
S73	276	("low" "lower" decrease decreasing improvement improve improving) near4 threshold and common adj ("source/drain" "S/D" source-drain (source near2 drain)) and @ad<"20040108"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:34
S74	151	("low" "lower" decrease decreasing improvement improve improving) near4 threshold and common adj ("source/drain" "S/D" source-drain (source near2 drain)) and @ad<"20040108" and memory and floating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:49
S75	559	common adj ("source/drain" "S/D" source-drain (source near2 drain)) and @ad<"20040108" and memory and floating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 23:58
S76	1	common adj ("source/drain" "S/D" source-drain (source near2 drain)) with pocket and @ad<"20040108" and memory and floating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 00:05
S77	1	"5751631".PN.	USPAT; USOCR	OR	OFF	2006/08/04 23:59
S78	1	"6074914".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:00
S79	1	"6074915".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:01
S80	1	"6103602".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:03
S81	1	"6103602".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:04
S82	1	common adj ("source/drain" "S/D" source-drain (source near2 drain)) same pocket and @ad<"20040108" and memory and floating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 00:07

S83	2	("5761121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 00:24
S84	1	"4404577".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:09
S85	1	"4425631".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:10
S86	1	"4630087".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:10
S87	1	"5089433".PN.	USPAT; USOCR	OR	OFF	2006/08/05 00:10
S88	0	buried with (counter-doped counter-doping oppositely) with (common adj (source near1 drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 00:25
S89	21	buried with (common adj (source near1 drain)) and floating and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 00:49
S90	126	(punch adj through punch-through) and common adj (source-drain source adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 01:13
S91	126	(punch adj through punch-through) and common adj (source-drain source adj drain "S/D")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 01:13
S92	5356	((p-type pmos pmosfet) near4 (memory floating adj gate)) "5912842".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 10:24
S93	1111	((p-type pmos pmosfet) near4 (memory floating adj gate) and common near1 (drain source)) "5912842".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 10:25
S94	197	((p-type pmos pmosfet) near4 (memory floating adj gate) and common near1 (drain source) and (implant pocket)) "5912842".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 11:17

S95	9	((p-type pmos pmosfet) near4 (memory floating adj gate) and common near1 (drain source) and halo) "5912842".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 11:21
S96	9	floating adj gate and select adj gate and (pocket implant) near10 (threhold adj voltage resistance resistivity) and (p-type adj channel p-type adj drain p-type source pmosfet pmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 11:39
S97	11	(("6861700") or ("7018895") or ("5284784") or ("6818512") or ("5824584")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 11:39
S98	3	("6909139").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 18:34
S99	420	(PMOS PMOSFET) and floating adj gate and select adj gate and threshold adj voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 18:36
S100	139	(PMOS PMOSFET) and floating adj gate and select adj gate and threshold adj voltage and (implant pocket)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 18:44
S101	19	(PMOS PMOSFET) and floating adj gate and select adj gate and threshold adj voltage and (implant pocket) and common near1 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 18:53
S102	1	(PMOS PMOSFET) and floating adj gate and select adj gate and (implant pocket) near20 common near1 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 18:56
S103	21	floating adj gate and select adj gate and (implant pocket) near20 common near1 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 18:56

S10 4	2456	257/315.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 21:34
S10 5	2001	257/315.ccls. and @pd>"19960401"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 21:34
S10 6	459	257/315.ccls. and @pd<"19960501"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 21:51
S10 7	1521	257/316.ccls. not 257/315.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/05 21:51
S10 8	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 07:20
S10 9	149	flash adj memory and (bbhe (hot adj electron) near4 band-to-band)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/06 07:49
S11 2	2389	((257/321) or (365/185.19) or (365/185.28)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 07:49
S11 3	42	S112 and flash adj memory and (hot adj electron near4 band-to-band)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 07:53
S11 4	46	S112 and flash adj memory and (BBHE (hot adj electron near4 band-to-band))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/06 07:55
S11 5	2	("6011725").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 07:57

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S11 7	1057	band-to-band adj tunneling	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 07:58
S11 8	3	"6610567"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/06 08:01
S11 9	2	("7078761").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 08:01
S12 0	1	"5736764".PN.	USPAT; USOCR	OR	OFF	2006/08/06 08:05
S12 1	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 11:57
S12 2	2	("20040070030").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/28 12:07
S12 3	163	(punch-through punchthrough) and select adj gate and floating and common near1 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/28 12:16
S12 4	253	select adj gate and floating adj gate and common near1 (source drain) and (pmos pmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/28 12:17
S12 5	47	("5687118").URPN.	USPAT	OR	OFF	2007/10/28 12:27
S12 6	18	("5914514").URPN.	USPAT	OR	OFF	2007/10/28 14:04
S12 7	4	"753673".ap.	USPAT	OR	OFF	2007/10/28 17:23